

# ZXMN2AM832

## MPPS™ Miniature Package Power Solutions DUAL 20V N-CHANNEL ENHANCEMENT MODE MOSFET

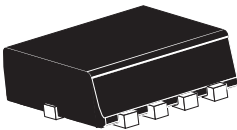
### SUMMARY

$V_{(BR)DSS} = 20V$ ;  $R_{DS(ON)} = 0.12\Omega$ ;  $I_D = 3A$

### DESCRIPTION

Packaged in the new innovative 3mm x 2mm MLP(Micro Leaded Package) outline this dual 20V N channel Trench MOSFET utilizes a unique structure combining the benefits of Low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage power management applications. Users will also gain several other **key benefits**:

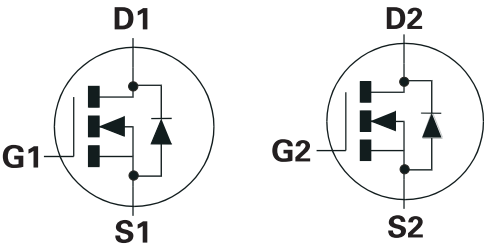
- Performance capability equivalent to much larger packages
- Improved circuit efficiency & power levels
- PCB area and device placement savings
- Reduced component count



3x2mm Dual Die MLP

### FEATURES

- Low On - Resistance
- Fast switching speed
- Low threshold
- Low gate drive
- 3mm x 2mm MLP



### APPLICATIONS

- DC-DC Converters
- Power Management Functions
- Disconnection switches
- Motor Control

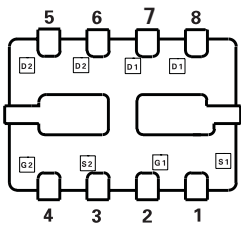
### ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXMN2AM832TA	7"	8mm	3000 units
ZXMN2AM832TC	13"	8mm	10000 units

### DEVICE MARKING

DNA

### PINOUT



3mm x 2mm Dual MLP  
underside view

# ZXMN2AM832

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	N-Channel	UNIT
Drain-Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current @ $V_{GS}=10V$ ; $T_A=25^\circ C$ <sup>(b) (f)</sup> @ $V_{GS}=10V$ ; $T_A=70^\circ C$ <sup>(b) (f)</sup> @ $V_{GS}=10V$ ; $T_A=25^\circ C$ <sup>(a) (f)</sup>	$I_D$	3.7	A
		3.0	A
		2.9	A
Pulsed Drain Current	$I_{DM}$	13	A
Continuous Source Current (Body Diode) <sup>(b) (f)</sup>	$I_S$	3.0	A
Pulsed Source Current (Body Diode)	$I_{SM}$	13	A
Power Dissipation at $T_A=25^\circ C$ <sup>(a) (f)</sup>	$P_D$	1.5	W
Linear Derating Factor		12	mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ <sup>(b) (f)</sup>	$P_D$	2.45	W
Linear Derating Factor		19.6	mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ <sup>(c) (f)</sup>	$P_D$	1	W
Linear Derating Factor		8	mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ <sup>(d) (f)</sup>	$P_D$	1.13	W
Linear Derating Factor		9	mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ <sup>(d) (g)</sup>	$P_D$	1.7	W
Linear Derating Factor		13.6	mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ <sup>(e) (g)</sup>	$P_D$	3	W
Linear Derating Factor		24	mW/ $^\circ C$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^\circ C$

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(f)	$R_{\theta JA}$	83.3	$^\circ C/W$
Junction to Ambient (b)(f)	$R_{\theta JA}$	51	$^\circ C/W$
Junction to Ambient (c)(f)	$R_{\theta JA}$	125	$^\circ C/W$
Junction to Ambient (d)(f)	$R_{\theta JA}$	111	$^\circ C/W$
Junction to Ambient (d)(g)	$R_{\theta JA}$	73.5	$^\circ C/W$
Junction to Ambient (e)(g)	$R_{\theta JA}$	41.7	$^\circ C/W$

### Notes

(a) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.

(b) Measured at  $t < 5$  secs for a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.

(c) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with minimal lead connections only**.

(d) For a dual device surface mounted on 10 sq cm single sided 1oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.

(e) For a dual device surface mounted on 85 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.

(f) For a dual device with one active die.

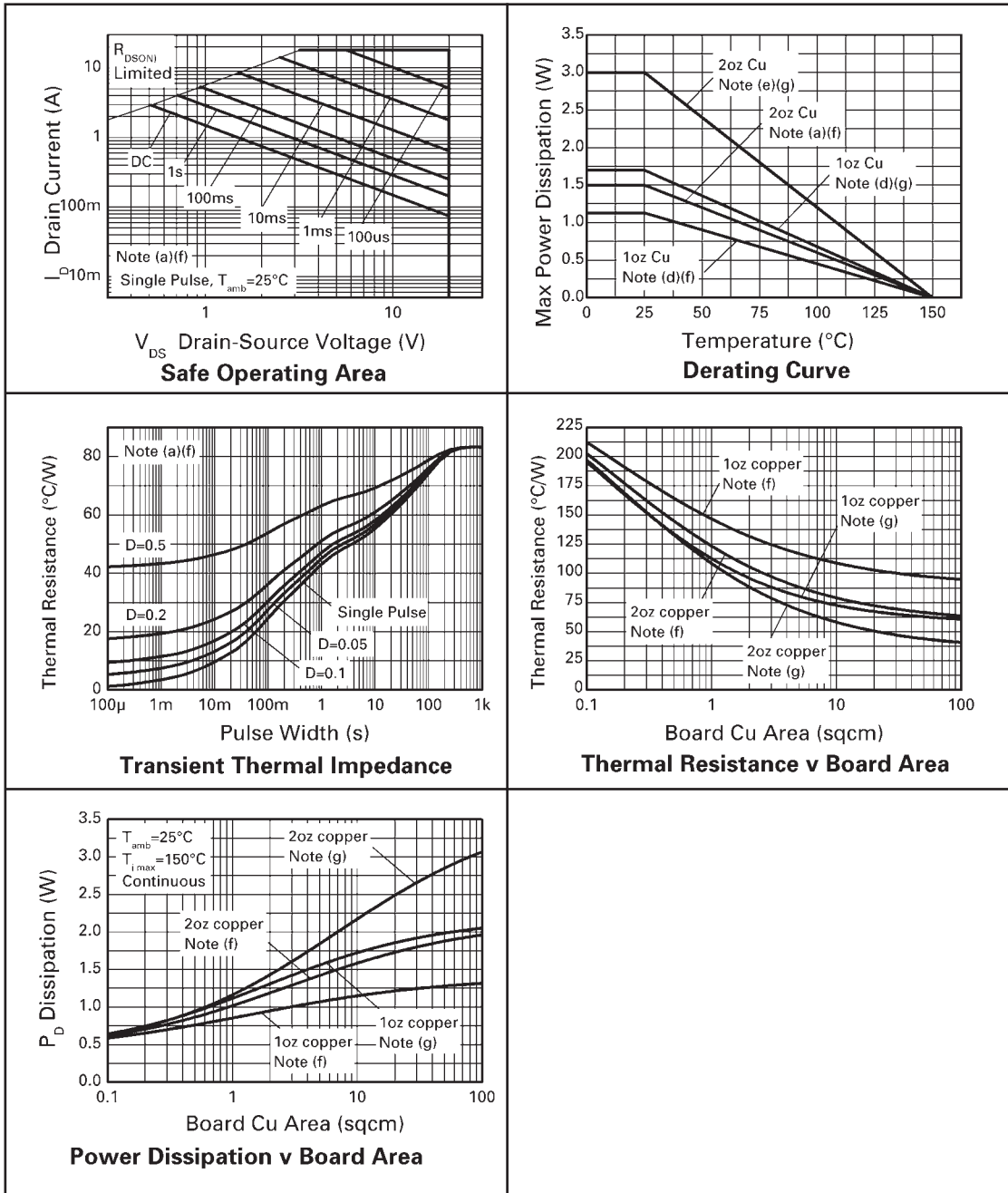
(g) For dual device with 2 active die running at equal power.

(h) Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.

(i) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device as shown in the package dimensions data. The thermal resistance for a dual device mounted on 1.5mm thick FR4 board using minimum copper 1 oz weight, 1mm wide tracks and one half of the device active is  $R_{th} = 250^\circ C/W$  giving a power rating of  $P_{tot} = 500mW$ .

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## TYPICAL CHARACTERISTICS



# ZXMN2AM832

**ELECTRICAL CHARACTERISTICS** (at  $T_{amb} = 25^{\circ}\text{C}$  unless otherwise stated).

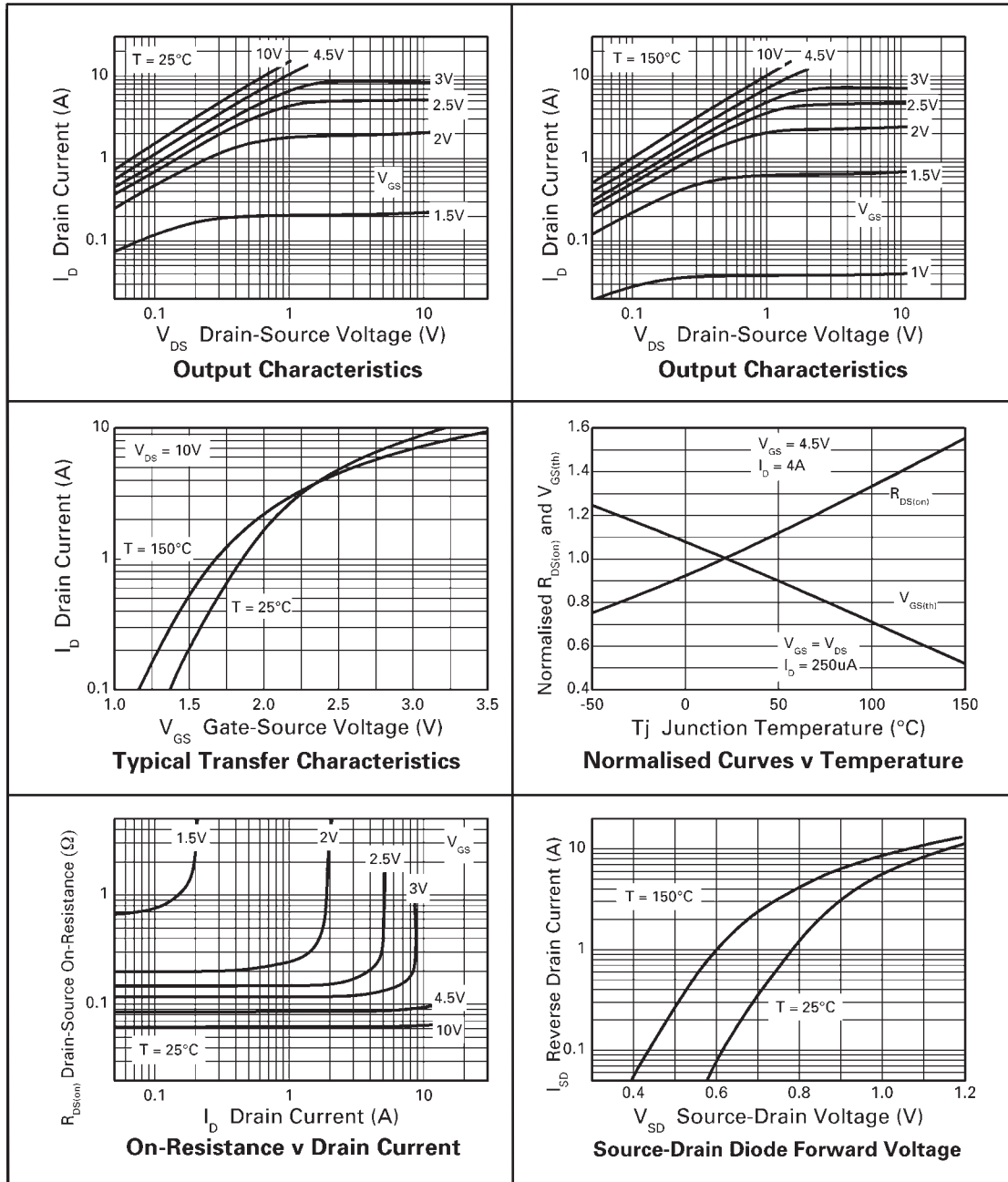
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	20			V	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1	μA	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V
Gate-Body Leakage	I <sub>GSS</sub>			100	nA	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	0.7			V	I <sub>D</sub> =250μA, V <sub>DS</sub> =V <sub>GS</sub>
Static Drain-Source On-State Resistance <sup>(1)</sup>	R <sub>DS(on)</sub>		0.09	0.12	Ω	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A
				0.30	Ω	V <sub>GS</sub> =2.5V, I <sub>D</sub> =1.5A
Forward Transconductance <sup>(3)</sup>	g <sub>fs</sub>		6.2		S	V <sub>DS</sub> =10V, I <sub>D</sub> =4A
DYNAMIC <sup>(3)</sup>						
Input Capacitance	C <sub>iss</sub>		299		pF	V <sub>DS</sub> =15 V, V <sub>GS</sub> =0V, f=1MHz
Output Capacitance	C <sub>oss</sub>		60		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		33		pF	
SWITCHING <sup>(2) (3)</sup>						
Turn-On Delay Time	t <sub>d(on)</sub>		2.31		ns	V <sub>DD</sub> =10V, I <sub>D</sub> =4A R <sub>G</sub> ≅6.0Ω, V <sub>GS</sub> =5V
Rise Time	t <sub>r</sub>		2.60		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>		1.55		ns	
Fall Time	t <sub>f</sub>		1.31		ns	
Total Gate Charge	Q <sub>g</sub>		3.1		nC	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A
Gate-Source Charge	Q <sub>gs</sub>		0.7		nC	
Gate-Drain Charge	Q <sub>gd</sub>		1.0		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage <sup>(1)</sup>	V <sub>SD</sub>		0.9	0.95	V	T <sub>J</sub> =25°C, I <sub>S</sub> =3.2A, V <sub>GS</sub> =0V
Reverse Recovery Time <sup>(3)</sup>	t <sub>rr</sub>		23		ns	T <sub>J</sub> =25°C, I <sub>F</sub> =4A, di/dt= 100A/μs
Reverse Recovery Charge <sup>(3)</sup>	Q <sub>rr</sub>		5.65		nC	

## NOTES

- (1) Measured under pulsed conditions. Width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .  
 (2) Switching characteristics are independent of operating junction temperature.  
 (3) For design aid only, not subject to production testing.

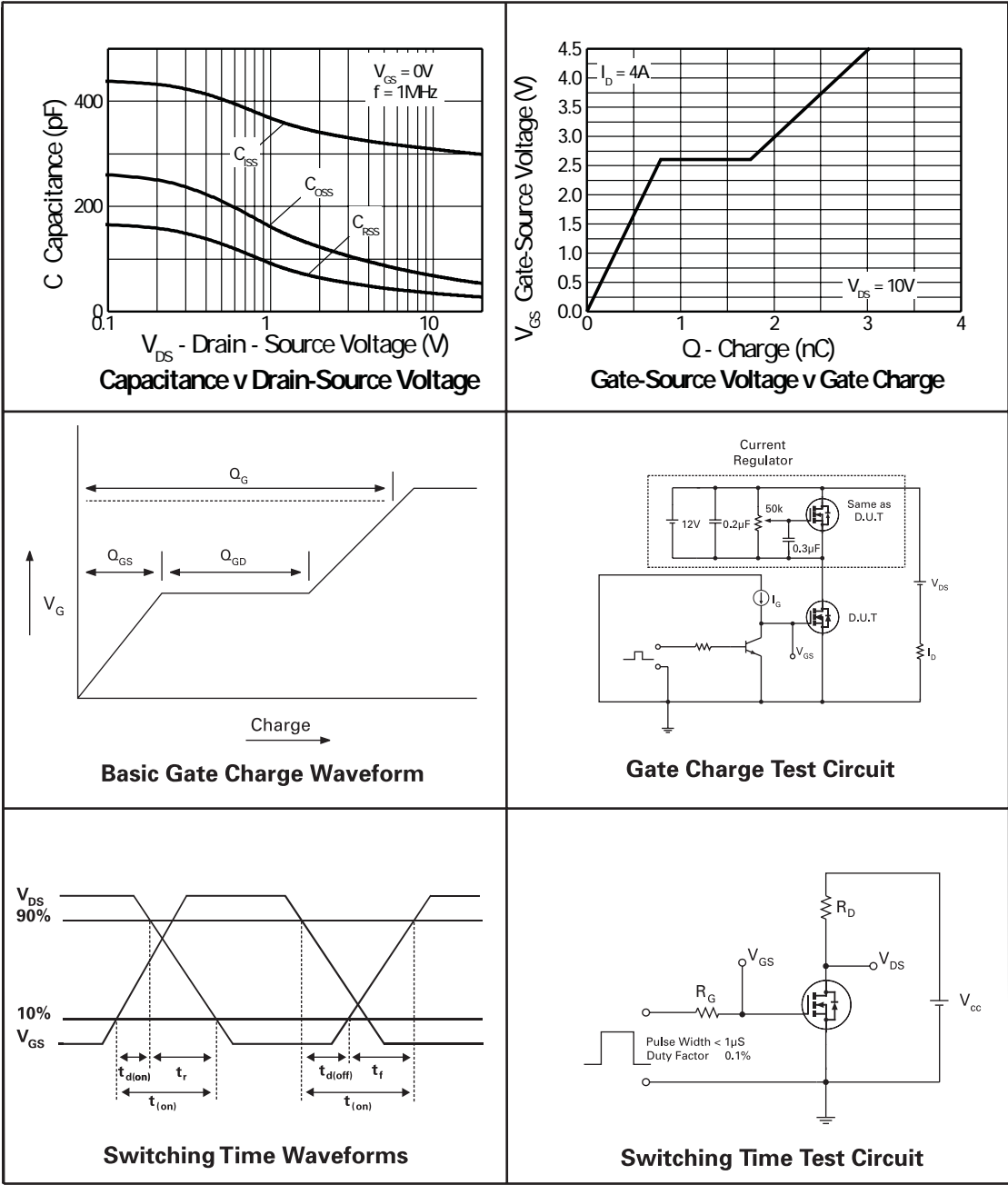
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## TYPICAL CHARACTERISTICS



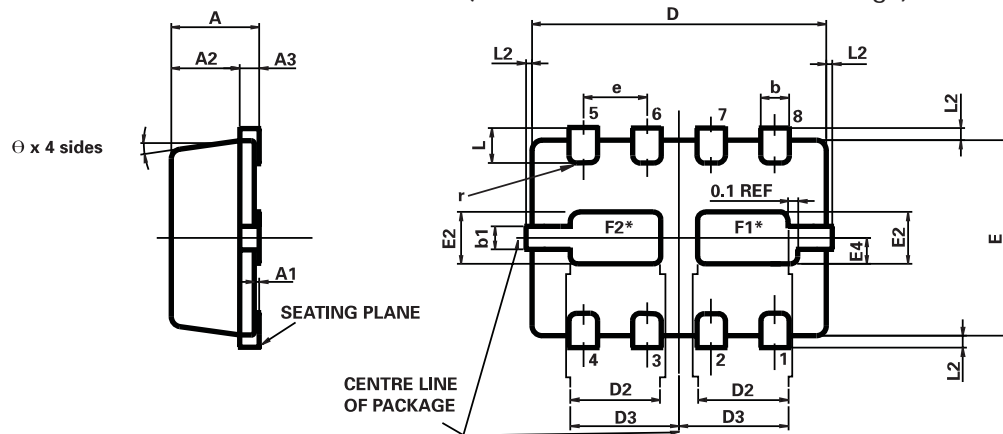
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## TYPICAL CHARACTERISTICS



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## MLP832 PACKAGE OUTLINE (3mm x 2mm Micro Leaded Package)



\*Exposed Flags. Solder connection to improve thermal dissipation is optional.  
F1 at collector 1 potential  
F2 at collector 2 potential

CONTROLLING DIMENSIONS IN MILLIMETRES  
APPROX. CONVERTED DIMENSIONS IN INCHES

### MLP832 PACKAGE DIMENSIONS

DIM	MILLIMETRES		INCHES		DIM	MILLIMETRES		INCHES	
	MIN.	MAX.	MIN.	MAX.		MIN.	MAX.	MIN.	MAX.
A	0.80	1.00	0.031	0.039	e	0.65 REF		0.0256 BSC	
A1	0.00	0.05	0.00	0.002	E	2.00 BSC		0.0787 BSC	
A2	0.65	0.75	0.0255	0.0295	E2	0.43	0.63	0.017	0.0249
A3	0.15	0.25	0.006	0.0098	E4	0.16	0.36	0.006	0.014
b	0.24	0.34	0.009	0.013	L	0.20	0.45	0.0078	0.0157
b1	0.17	0.30	0.0066	0.0118	L2	0.125	0.125	0.00	0.005
D	3.00 BSC		0.118 BSC		r	0.075 BSC		0.0029 BSC	
D2	0.82	1.02	0.032	0.040	Θ	0°	12°	0°	12°

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany  Telephone: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 <a href="mailto:europa.sales@zetex.com">europa.sales@zetex.com</a>	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA  Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 <a href="mailto:usa.sales@zetex.com">usa.sales@zetex.com</a>	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong  Telephone: (852) 26100 611 Fax: (852) 24250 494 <a href="mailto:asia.sales@zetex.com">asia.sales@zetex.com</a>	Zetex Semiconductors plc Zetex Technology Park Chadderton, Oldham, OL9 9LL United Kingdom  Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 <a href="mailto:hq@zetex.com">hq@zetex.com</a>

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